

# isc N-Channel MOSFET Transistor

### **IRF1405S**

#### • FEATURES

- With TO-263( D2PAK ) packaging
- · High speed switching
- · Low gate input resistance
- · Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



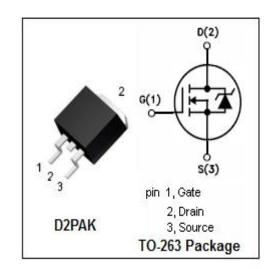
- Power supply
- · Switching applications

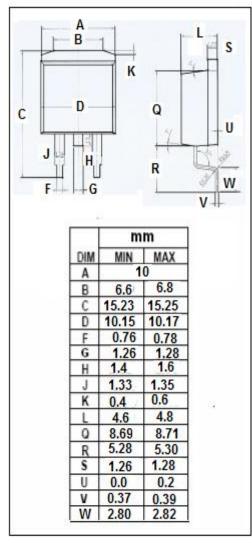


| SYMBOL           | PARAMETER                                  | VALUE     | UNIT          |  |
|------------------|--|-----------|---------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 55        | V             |  |
| $V_{GSS}$        | Gate-Source Voltage                        | ±20       | V             |  |
| I <sub>D</sub>   | Drain Current-Continuous;Tc=25℃<br>Tc=100℃ | 131<br>98 | А             |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 680       | А             |  |
| $P_D$            | Total Dissipation                          | 200       | W             |  |
| Tj               | Operating Junction Temperature             | 175       | ${\mathbb C}$ |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~175   | ${\mathbb C}$ |  |

#### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |      | UNIT |  |
|-----------|---------------------------------------|------|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 0.75 | °C/W |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 40   | °C/W |  |





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX       | UNIT       |
|---------------------|--------------------------------|--|-----|-----|-----------|------------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA   | 55  |     |           | V          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA  | 2.0 |     | 4.0       | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =101A  |     | 4.6 | 5.3       | mΩ         |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> =±20V;V <sub>DS</sub> = 0V   |     |     | ±0.2      | μ <b>А</b> |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =55V; V <sub>GS</sub> = 0V;Tc=25°C<br>V <sub>DS</sub> =44V; V <sub>GS</sub> = 0V; Tc=125°C |     |     | 20<br>250 | μ <b>А</b> |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =101A, V <sub>GS</sub> = 0 V   |     |     | 1.3       | V          |



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